Anton Gutakovskii

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

222 papers	1,749 citations	19 h-index	29 g-index
231 ext. papers	2,017 ext. citations	2 avg, IF	4.41 L-index

#	Paper	IF	Citations
222	Al2O3/InGaAs interface passivation by fluorine-containing anodic layers. *Journal of Applied Physics*, **2022**, 131, 085301	2.5	
221	Si-based light emitters synthesized with Ge+ ion bombardment. *Journal of Applied Physics*, **2021**, 130, 153101	2.5	0
220	Robust semiconductor-on-ferroelectric structures with hafnia–zirconia–lumina UTBOX stacks compatible with CMOS technology. *Journal Physics D: Applied Physics*, **2021**, 54, 225101	3	2
219	Extraction of the components of effective mobility in thin films. *Journal Physics D: Applied Physics*, **2021**, 54, 255105	3	0
218	Specific Features of the Atomic Structure of Iron Silicide Nanocrystals in a Silicon Matrix. *Crystallography Reports*, **2021**, 66, 601-607	0.6	
217	Epitaxial growth of peculiar GeSn and SiSn nanostructures using a Sn island array as a seed. *Applied Surface Science*, **2021**, 553, 149572	6.7	3
216	Synthesis of crystalline Mg2Si films by ultrafast deposition of Mg on Si(111) and Si(001) at high temperatures. Mg/Si intermixing and reaction mechanisms. *Materials Chemistry and Physics*, **2021**, 258, 123903	4.4	0
215	Selective MOCVD synthesis of VO2 crystals on nanosharp Si structures. *CrystEngComm*, **2021**, 23, 443-452	3.3	0
214	Resistive switching on individual VO nanoparticles encapsulated in fluorinated graphene films. *Physical Chemistry Chemical Physics*, **2021**, 23, 20434-20443	3.6	1
213	Effect of the structure and the phase composition on the mechanical properties of Al–Cu–Li alloy laser welds. *Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing*, **2021**, 809, 140947	5.3	2
212	Structural Transformations of the Dislocation Cores in Si and Their Relationship with Photoluminescence. *Crystallography Reports*, **2021**, 66, 636-643	0.6	
211	Extended Defects in O+-Implanted Si Layers and Their Luminescence. *Crystallography Reports*, **2021**, 66, 625-635	0.6	1
210	Transformation of the InP(001) surface upon annealing in an arsenic flux. *Surface Science*, **2021**, 710, 121861	1.8	4
209	Blister suppression in the CO+ molecule implanted SOI substrates with ultrathin buried oxides. *Materials Today Communications*, **2021**, 28, 102498	2.5	
208	Effect of embedding of CrSi2 and –FeSi2 nanocrystals into n-type conductivity silicon on the transport and thermal generation of carriers. *Applied Surface Science*, **2021**, 566, 150620	6.7	
207	Fluorinated graphene nanoparticles with 1-3 nm electrically active graphene quantum dots. *Nanotechnology*, **2020**, 31, 295602	3.4	5
206	Electron-nuclei interaction in the X valley of (In,Al)As/AlAs quantum dots. *Physical Review B*, **2020**, 101,	3.3	3

205	Effect of Sn for the dislocation-free SiSn nanostructure formation on the vapor-liquid-crystal mechanism. *AIP Advances*, **2020**, 10, 015309	1.5	2
204	Formation and thermoelectric properties of the n- and p-type silicon nanostructures with embedded GaSb nanocrystals. *Japanese Journal of Applied Physics*, **2020**, 59, SFFB04	1.4	1
203	A new approach to the fabrication of VO nanoswitches with ultra-low energy consumption. *Nanoscale*, **2020**, 12, 3443-3454	7.7	5
202	Probing the Mg2Si/Si(1 1 1) heterojunction for photovoltaic applications. *Solar Energy*, **2020**, 211, 383-395	3.8	8
201	Resonant plasmon enhancement of light emission from CdSe/CdS nanoplatelets on Au nanodisk arrays. *Journal of Chemical Physics*, **2020**, 153, 164708	3.9	3
200	Forming Dislocation Pairs in the Ge/GeSi/Si(001) Heterostructure. *Physics of the Solid State*, **2019**, 61, 145-148	0.8	
199	GaAs/GaP Quantum-Well Heterostructures Grown on Si Substrates. *Semiconductors*, **2019**, 53, 1143-1147	0.7	4
198	Electron Paramagnetic Resonance in Ge/Si Heterostructures with Mn-Doped Quantum Dots. *JETP Letters*, **2019**, 109, 270-275	1.2	
197	Bimetallic Pt,Ir-containing coatings formed by MOCVD for medical applications. *Journal of Materials Science: Materials in Medicine*, **2019**, 30, 69	4.5	5
196	Structure of Hf0.9La0.1O2 Ferroelectric Films Obtained by the Atomic Layer Deposition. *JETP Letters*, **2019**, 109, 116-120	1.2	3
195	Resistive Switching Effect with ON/OFF Current Relation up to 109 in 2D Printed Composite Films of Fluorinated Graphene with V2O5 Nanoparticles. *Advanced Electronic Materials*, **2019**, 5, 1900310	6.4	3
194	Silicon p+-n Diodes with Embedded β-FeSi2 and CrSi2 Nanocrystals: Morphology, Crystal Structure and Photoelectric Properties. *International Journal of Nanoscience*, **2019**, 18, 1940084	0.6	2
193	An Influence of the Si(111)3-4o Vicinal Surface on the Solid Phase Epitaxy of β-FeSi2 Nanorods and their Crystal Parameters. *Key Engineering Materials*, **2019**, 806, 30-35	0.4	1
192	Silicide phase formation by Mg deposition on amorphous Si. Ab initio calculations, growth process and thermal stability. *Journal of Alloys and Compounds*, **2019**, 778, 514-521	5.7	2
191	Fluorinated graphene suspension for flexible and printed electronics: Flakes, 2D films, and heterostructures. *Materials and Design*, **2019**, 164, 107526	8.1	16
190	Atomic and electronic structure of ferroelectric La-doped HfO2 films. *Materials Research Express*, **2019**, 6, 036403	1.7	8
189	Pseudomorphic GeSiSn, SiSn and Ge layers in strained heterostructures. *Nanotechnology*, **2018**, 29, 154002	3.4	16
188	Different electrochemical responses of LiFe0.5Mn0.5PO4 prepared by mechanochemical and solvothermal methods. *Journal of Alloys and Compounds*, **2018**, 742, 454-465	5.7	10

187	Charge Berezinskii-Kosterlitz-Thouless transition in superconducting NbTiN films. *Scientific Reports*, **2018**, 8, 4082	4.9	18
186	Heterostructures with diffused interfaces: Luminescent technique for ascertainment of band alignment type. *Journal of Applied Physics*, **2018**, 123, 115701	2.5	8
185	High-Resolution Electron Microscopy Investigations of Structure and Morphology of Cadmium Selenide Nanocrystals. *Russian Physics Journal*, **2018**, 61, 509-515	0.7	
184	Aluminum-induced crystallization of silicon suboxide thin films. *Applied Physics A: Materials Science and Processing*, **2018**, 124, 1	2.6	8
183	On the structure and photoluminescence of dislocations in silicon. *Journal of Applied Physics*, **2018**, 124, 053106	2.5	6
182	Influence of a Low-Temperature GaAs Dislocation Filter on the Perfection of GaAs/Si Layers. *Optoelectronics, Instrumentation and Data Processing*, **2018**, 54, 181-186	0.6	3
181	Optically detected magnetic resonance of photoexcited electrons in (In,Al)As/AlAs quantum dots with indirect band gap and type-I band alignment. *Physical Review B*, **2018**, 97,	3.3	6
180	Spinodal Decomposition in InSb/AlAs Heterostructures. *Semiconductors*, **2018**, 52, 1392-1397	0.7	1
179	Formation of a Thin Continuous GaSb Film on Si(001) by Solid Phase Epitaxy. *Nanomaterials*, **2018**, 8,	5.4	4
178	Self-assembled strained GeSiSn nanoscale structures grown by MBE on Si(100). *Journal of Crystal Growth*, **2017**, 457, 215-219	1.6	3
177	A room-temperature-operated Si LED with β-FeSi2 nanocrystals in the active layer: W emission power at 1.5 μm. *Journal of Applied Physics*, **2017**, 121, 113101	2.5	10
176	Determining the structure of energy in heterostructures with diffuse interfaces. *Bulletin of the Russian Academy of Sciences: Physics*, **2017**, 81, 1052-1057	0.4	1
175	Stress-induced indirect to direct band gap transition in β-FeSi2 nanocrystals embedded in Si **2017**,		1
174	Electron Microscopy Study of Metal Sulfide Nanocrystals Formed in Langmuir–Blodgett Films. *Nanotechnologies in Russia*, **2017**, 12, 369-375	0.6	3
173	Photoluminescence associated with {113} defects in oxygen-implanted silicon. *Physica Status Solidi (A) Applications and Materials Science*, **2017**, 214, 1700317	1.6	7
172	Photoluminescence spectroscopy investigation of epitaxial Si/GaSb nanocrystals/Si heterostructure **2017**,		1
171	Sn influence on MBE growth of GeSiSn/Si MQW. *Journal of Physics: Conference Series*, **2017**, 816, 012020	0.3	3
170	MBE-grown InSb photodetector arrays. *Technical Physics*, **2017**, 62, 915-919	0.5	2

169	Nature of luminescence of PbS quantum dots synthesized in a Langmuir–Blodgett matrix. *JETP Letters*, **2017**, 106, 18-22	1.2	
168	Strain in Ultrathin SiGeSn Layers in a Silicon Matrix. *JETP Letters*, **2017**, 106, 780-784	1.2	
167	Formation of low-dimensional structures in the InSb/AlAs heterosystem. *Semiconductors*, **2017**, 51, 1233–1239	0.7	3
166	Effect of synthesis conditions on the structure and properties of new SiC x N y M z materials for spintronics. *Journal of Structural Chemistry*, **2017**, 58, 1493-1502	0.9	2
165	Peculiarities of structure, morphology, and electrochemistry of the doped 5-V spinel cathode materials LiNi0.5-x Mn1.5-y M x+y O4 (M = Co, Cr, Ti; x+y = 0.05) prepared by mechanochemical way. *Journal of Solid State Electrochemistry*, **2016**, 20, 235-246	2.6	7
164	Quantum dots formed in InSb/AlAs and AlSb/AlAs heterostructures. *JETP Letters*, **2016**, 103, 692-698	1.2	8
163	Experimental observation of motion of edge dislocations in Ge/Ge x Si1−x /Si(001) (x = 0.2–0.6) heterostructures. *Journal of Experimental and Theoretical Physics*, **2016**, 123, 832-837	1	2
162	Surface-enhanced Raman spectroscopy of semiconductor nanostructures. *Physica E: Low-Dimensional Systems and Nanostructures*, **2016**, 75, 210-222	3	17
161	Structural and morphological features of ultrathin epitaxial InSb films in AlAs matrix. *Journal of Physics: Conference Series*, **2016**, 769, 012030	0.3	
160	Strained multilayer structures with pseudomorphic GeSiSn layers. *Semiconductors*, **2016**, 50, 1584-1588	0.7	5
159	Apoptosis-mediated endothelial toxicity but not direct calcification or functional changes in anti-calcification proteins defines pathogenic effects of calcium phosphate bions. *Scientific Reports*, **2016**, 6, 27255	4.9	22
158	Structure and morphology of InSb epitaxial films in the AlAs matrix. *Nanotechnologies in Russia*, **2016**, 11, 12-19	0.6	1
157	Influence of the additional p+ doped layers on the properties of AlGaAs/InGaAs/AlGaAs heterostructures for high power SHF transistors. *Journal Physics D: Applied Physics*, **2016**, 49, 095108	3	9
156	Formation and crystal structure of GaSb/GaP quantum dots. *Bulletin of the Russian Academy of Sciences: Physics*, **2016**, 80, 17-22	0.4	4
155	Experimental observation of the dislocation walls in heterostructures with two interfaces: Ge/Ge0.5Si0.5 10 nm/Si(001) as an example. *Philosophical Magazine Letters*, **2016**, 96, 361-366	1	1
154	Unexpected travel of Lomer-type dislocations in Ge/GexSi1-x/Si(001) heterostructures. *Thin Solid Films*, **2016**, 616, 348-350	2.2	4
153	Raman, AFM, and TEM profiling of QD multilayer structures. *Materials Research Express*, **2015**, 2, 035003	1.7	5
152	Linear chains of Ge/Si quantum dots grown on a prepatterned surface formed by ion irradiation. *Semiconductors*, **2015**, 49, 749-752	0.7	13

151	Electroluminescent 1.5-□m light-emitting diodes based on p +-Si/NC □FeSi2/n-Si structures. *Semiconductors*, **2015**, 49, 508-512	0.7	1
150	Role of edge dislocations in plastic relaxation of GeSi/Si(001) heterostructures: Dependence of introduction mechanisms on film thickness. *Physics of the Solid State*, **2015**, 57, 765-770	0.8	2
149	High-quality single-crystal diamond-graphite-diamond membranes and devices. *International Journal of Nanotechnology*, **2015**, 12, 226	1.5	6
148	InAs-based metal-oxide-semiconductor structure formation in low-energy Townsend discharge. *Applied Physics Letters*, **2015**, 107, 173501	3.4	14
147	Ferromagnetic HfO2/Si/GaAs interface for spin-polarimetry applications. *Applied Physics Letters*, **2015**, 107, 123506	3.4	5
146	Enhancement of the Si p-n diode NIR photoresponse by embedding □FeSi2 nanocrystallites. *Scientific Reports*, **2015**, 5, 14795	4.9	19
145	Hemozoin "knobs" in Opisthorchis felineus infected liver. *Parasites and Vectors*, **2015**, 8, 459	4	11
144	InAsSb on GaAs (001): influence of the arsenic molecules form on composition and crystalline properties of MBE layers. *Journal of Physics: Conference Series*, **2015**, 643, 012006	0.3	2
143	The convenient preparation of stable aryl-coated zerovalent iron nanoparticles. *Beilstein Journal of Nanotechnology*, **2015**, 6, 1192-8	3	15
142	Specific features of plastic relaxation of a metastable Ge x Si1 □x layer buried between a silicon substrate and a relaxed germanium layer. *Physics of the Solid State*, **2014**, 56, 247-253	0.8	5
141	LiVPO4F/Li3V2(PO4)3 nanostructured composite cathode materials prepared via mechanochemical way. *Journal of Solid State Electrochemistry*, **2014**, 18, 1389-1399	2.6	22
140	Analysis of the dislocation structure at the Ge/Si(111) heterointerface. *Journal of Surface Investigation*, **2014**, 8, 787-793	0.5	4
139	Heteroepitaxy of AIIIBV films on vicinal Si(001) substrates. *Optoelectronics, Instrumentation and Data Processing*, **2014**, 50, 224-233	0.6	2
138	Atomic structure of extended defects in boron-implanted silicon layers. *Optoelectronics, Instrumentation and Data Processing*, **2014**, 50, 241-246	0.6	
137	Electron microscopic studies of CuS nanocrystals formed in Langmuir-Blodgett films. *Optoelectronics, Instrumentation and Data Processing*, **2014**, 50, 304-309	0.6	3
136	Synthesis and Characterization of CuxS (x = 1□2) Nanocrystals Formed by the Langmuir□Blodgett Technique. *Journal of Physical Chemistry C*, **2014**, 118, 23409-23414	3.8	40
135	Formation of Mg silicides on amorphous Si. Origin and role of high pressure in the film growth. *Materials Chemistry and Physics*, **2014**, 148, 1078-1082	4.4	5
134	Coexistence of type-I and type-II band alignment in Ga(Sb, P)/GaP heterostructures with pseudomorphic self-assembled quantum dots. *JETP Letters*, **2014**, 99, 76-81	1.2	5

133	Oxide-free InAs(111)A interface in metal-oxide-semiconductor structure with very low density of states prepared by anodic oxidation. *Applied Physics Letters*, **2014**, 105, 161601	3.4	12
132	Structure and Optical Properties of Ca Silicide Films and Si/Ca3Si4/Si(111) Heterostructures. *Solid State Phenomena*, **2014**, 213, 71-79	0.4	4
131	Dislocation interaction of layers in the Ge/Ge-seed/GexSi1−x/Si(0 0 1) (x ~ 0.3−0.5) system: Trapping of misfit dislocations on the Ge-seed/GeSi interface. *Acta Materialia*, **2013**, 61, 5400-5405	8.4	10
130	High-precision nanoscale length measurement. *Nanotechnologies in Russia*, **2013**, 8, 518-531	0.6	6
129	Electroluminescence properties of p-Si/β-FeSi2 NCs/n-Si mesa diodes with embedded multilayers of β-FeSi2 nanocrystallites. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2013**, 10, 1850-1853		
128	Brief observe on iron silicide growth on amorphous silicon. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2013**, 10, 1742-1745		3
127	Surface-enhanced Raman scattering by semiconductor nanostructures. *Optoelectronics, Instrumentation and Data Processing*, **2013**, 49, 504-513	0.6	3
126	Dual threshold diode based on the superconductor-to-insulator transition in ultrathin TiN films. *Applied Physics Letters*, **2013**, 102, 042601	3.4	7
125	Formation of iron and iron silicides on silicon and iron surfaces. Role of the deposition rate and volumetric effects. *Applied Physics A: Materials Science and Processing*, **2013**, 112, 507-515	2.6	7
124	Magnetic field-induced dissipation-free state in superconducting nanostructures. *Nature Communications*, **2013**, 4, 1437	17.4	75
123	Mechanism of induced nucleation of misfit dislocations in the Ge-on-Si(0 0 1) system and its role in the formation of the core structure of edge misfit dislocations. *Acta Materialia*, **2013**, 61, 617-621	8.4	23
122	CdZnS quantum dots formed by the Langmuir–Blodgett technique. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2013**, 31, 04D109	1.3	13
121	The mechanism of {113} defect formation in silicon: clustering of interstitial-vacancy pairs studied by in situ high-resolution electron microscope irradiation. *Microscopy and Microanalysis*, **2013**, 19 Suppl 5, 38-42	0.5	12
120	Ge and GexSi1−x islands formation on GexSi1−x solid solution surface. *Thin Solid Films*, **2012**, 520, 3319-3321	2.2	2
119	Evolution of silicon nanoclusters and hydrogen in SiNx:H films: Influence of high hydrostatic pressure under annealing. *Thin Solid Films*, **2012**, 520, 6207-6214	2.2	10
118	Structural state of Ge/Si heterosystems with (001), (111), and (7 7 10) interfaces. *Bulletin of the Russian Academy of Sciences: Physics*, **2012**, 76, 325-327	0.4	4
117	Decomposition of a supersaturated solid solution of Fe in GaAs. *Inorganic Materials*, **2012**, 48, 93-95	0.9	3
116	Edge misfit dislocations in the GeSi/Si(001) pair: Conditions and specific features of high-quantity generation. *Journal of Crystal Growth*, **2012**, 338, 12-15	1.6	4

115	Novel self-assembled quantum dots in the GaSb/AlAs heterosystem. *JETP Letters*, **2012**, 95, 534-536	1.2	8
114	Preparation of thin films of platinum group metals by pulsed MOCVD. I. Deposition of Ir layers. *Journal of Structural Chemistry*, **2012**, 53, 715-724	0.9	13
113	Preparation of thin films of platinum group metals by pulsed MOCVD. II. Deposition of Ru layers. *Journal of Structural Chemistry*, **2012**, 53, 725-733	0.9	7
112	Initial stage growth of GexSi1-x layers and Ge quantum dot formation on GexSi1-x surface by MBE. *Nanoscale Research Letters*, **2012**, 7, 561	5	13
111	New system of self-assembled GaSb/GaP quantum dots. *Semiconductors*, **2012**, 46, 1534-1538	0.7	7
110	Influence of shape of GaN/AlN quantum dots on luminescence decay law. *Physica Status Solidi (A) Applications and Materials Science*, **2012**, 209, 653-656	1.6	4
109	Atomic structure and energy spectrum of Ga(As,P)/GaP heterostructures. *Journal of Applied Physics*, **2012**, 112, 083713	2.5	17
108	Crystallization of amorphous Si nanoclusters in SiO(x) films using femtosecond laser pulse annealings. *Journal of Nanoscience and Nanotechnology*, **2012**, 12, 8694-9	1.3	10
107	Non-linear conduction in the critical region of the superconductor-insulator transition in TiN thin films. *Journal of Physics: Conference Series*, **2012**, 400, 022042	0.3	1
106	Optical property improvement of InAs/GaAs quantum dots grown by hydrogen-plasma-assisted molecular beam epitaxy. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2011**, 29, 03C127	1.3	3
105	High-quality structures with InAs/Al0.9Ga0.1As QDs produced by droplet epitaxy. *Journal of Crystal Growth*, **2011**, 337, 93-96	1.6	2
104	Exciton recombination dynamics in an ensemble of (In,Al)As/AlAs quantum dots with indirect band-gap and type-I band alignment. *Physical Review B*, **2011**, 84,	3.3	30
103	Spontaneous composition modulation during Cd x Hg1 Te(301) molecular beam epitaxy. *JETP Letters*, **2011**, 94, 324-328	1.2	4
102	Growth, structure and luminescence properties of multilayer Si/FeSi2NCs/Si/Si nanoheterostructures. *Thin Solid Films*, **2011**, 519, 8480-8484	2.2	12
101	Defects in the crystal structure of Cd x Hg1 x Te layers grown on the Si (310) substrates. *Semiconductors*, **2011**, 45, 926-934	0.7	9
100	Edge misfit dislocations in Ge x Si1 x /Si(001) (x ~ 1) heterostructures: role of buffer Ge y Si1 y (y Physics of the Solid State, **2011**, 53, 1791-1797	0.8	3
99	Strained germanium films in Ge/InGaAs/GaAs heterostructures: Formation of edge misfit dislocations at the Ge/InGaAs interface. *Physics of the Solid State*, **2011**, 53, 2005-2011	0.8	4
98	Inclined misfit dislocations in a film/substrate system. *Physica Status Solidi (A) Applications and Materials Science*, **2011**, 208, 1896-1901	1.6	

97	Mechanisms of edge-dislocation formation in strained films of zinc blende and diamond cubic semiconductors epitaxially grown on (001)-oriented substrates. *Journal of Applied Physics*, **2011**, 109, 123519	2.5	22
96	On triple dislocation nodes observed by TEM in a Ge0.4Si0.6 film grown on a slightly deviating (0 0 1)Si substrate. *Philosophical Magazine Letters*, **2011**, 91, 510-515	1	
95	Role of cross-slipping in formation of edge dislocations in heteroepitaxial systems GeSi-on-Si(001) and Ge-on-InGaAs/GaAs. *Philosophical Magazine Letters*, **2011**, 91, 458-464	1	1
94	Initial stages of Ge epitaxy on Si(111) under quasi-equilibrium growth conditions. *JETP Letters*, **2010**, 92, 388-395	1.2	11
93	Formation of edge misfit dislocations in GexSi1-x(x~0.4-0.8) films grown on misoriented (001)->(111) Si substrates: Features before and after film annealing. *Journal of Applied Physics*, **2010**, 107, 123521	2.5	9
92	High quality relaxed GaAs quantum dots in GaP matrix. *Applied Physics Letters*, **2010**, 97, 023108	3.4	20
91	Precise surface measurements at the nanoscale. *Measurement Science and Technology*, **2010**, 21, 054004	2	14
90	Nonradiative energy transfer between vertically coupled indirect and direct bandgap InAs quantum dots. *Applied Physics Letters*, **2010**, 97, 263102	3.4	9
89	Heteroepitaxy of Ge x Si1 -x (x ~ 0.4-0.5) films on Si(001) substrates misoriented to (111): Formation of short edge misfit dislocations alone in the misorientation direction. *Physics of the Solid State*, **2010**, 52, 32-36	0.8	3
88	Precise measurements of nanostructure parameters. *Optoelectronics, Instrumentation and Data Processing*, **2010**, 46, 301-311	0.6	2
87	Specific features of formation and propagation of 60-and 90-misfit dislocations in GexSi1-x/Si films with x>0.4. *Journal of Crystal Growth*, **2010**, 312, 3080-3084	1.6	11
86	Potentialities and basic principles of controlling the plastic relaxation of GeSi/Si and Ge/Si films with stepwise variation in the composition **2010**, 42, 1		
85	Crystal perfection of GaP films grown on Si substrates by solid-source MBE with atomic hydrogen. *Semiconductors*, **2009**, 43, 1235-1239	0.7	3
84	Atomic and energy structure of InAs/AlAs quantum dots. *Physical Review B*, **2008**, 78,	3.3	42
83	Investigation of multilayer silicon structures with buried iron silicide nanocrystallites: growth, structure, and properties. *Journal of Nanoscience and Nanotechnology*, **2008**, 8, 527-34	1.3	4
82	Features of formation and propagation of 60-and 90-misfit dislocations in GexSi1-xSi (x~0.4-0.5) films caused by Si substrate misorientation from (001). *Applied Physics Letters*, **2008**, 92, 131901	3.4	16
81	Formation of edge misfit dislocations in GexSi1-x (x~0.4-0.5) films grown on misoriented (001)->(111) Si substrates. *Journal of Crystal Growth*, **2008**, 310, 3422-3427	1.6	14
80	The influence of elastic strains on the growth and properties of vertically ordered Ge-Si-Ge clusters. *Thin Solid Films*, **2008**, 517, 69-70	2.2	1

79	Pulsed ion-beam assisted deposition of Ge nanocrystals on SiO2 for non-volatile memory device. *Thin Solid Films*, **2008**, 517, 313-316	2.2	5
78	Potentialities and basic principles of controlling the plastic relaxation of GeSi/Si and Ge/Si films with stepwise variation in the composition. *Semiconductors*, **2008**, 42, 1-20	0.7	18
77	Effect of the ion-energy loss rate on defect formation during implantation in silicon nanocrystals. *Semiconductors*, **2008**, 42, 1127-1131	0.7	3
76	Formation of misfit edge dislocations in Ge x Si1 □x films (x ~ 0.4□0.5) grown on tilted Si(001) -> (111) substrates. *Physics of the Solid State*, **2008**, 50, 1857-1861	0.8	3
75	Role of the dislocation screw component in the formation of the dislocation structure in Ge- and Si-based semiconductor heterosystems. *Journal of Surface Investigation*, **2007**, 1, 247-254	0.5	3
74	Morphological transformations of vanadium oxide films during low-temperature reduction in hydrogen electron cyclotron resonance plasma. *Journal of Surface Investigation*, **2007**, 1, 454-461	0.5	6
73	Structure and electrical properties of polycrystalline SiGe films grown by molecular beam deposition. *Semiconductors*, **2007**, 41, 341-344	0.7	1
72	Formation, crystal structure, and properties of silicon with buried iron disilicide nanocrystallites on Si (100) substrates. *Semiconductors*, **2007**, 41, 1067-1073	0.7	3
71	Plastic relaxation of GeSi/Si(001) films grown by molecular-beam epitaxy in the presence of the Sb surfactant. *Semiconductors*, **2007**, 41, 1234-1239	0.7	4
70	Application of high-resolution electron microscopy for visualization and quantitative analysis of strain fields in heterostructures. *Bulletin of the Russian Academy of Sciences: Physics*, **2007**, 71, 1426-1432	0.4	33
69	Silicon layers atop iron silicide nanoislands on Si(100) substrate: Island formation, silicon growth, morphology and structure. *Thin Solid Films*, **2007**, 515, 7805-7812	2.2	3
68	VARIATION OF IN-PLANE LATTICE CONSTANT OF Si/Ge/Si HETEROSTRUCTURES WITH Ge QUANTUM DOTS. *International Journal of Nanoscience*, **2007**, 06, 297-299	0.6	2
67	Pulsed ion-beam induced nucleation and growth of Ge nanocrystals on SiO2. *Applied Physics Letters*, **2007**, 90, 133120	3.4	12
66	New Compositionally-Ordered GeSi Nano Dots Fabricated with 1250 keV Electrons. *Advanced Materials Research*, **2007**, 26-28, 1195-1198	0.5	2
65	Pulsed Low-energy Ion-beam Induced Nucleation and Growth of Ge Nanocrystals on SiO2. *Materials Research Society Symposia Proceedings*, **2007**, 1020, 1		
64	Strong sensitivity of photoluminescence of InAs/AlAs quantum dots to defects: evidence for lateral inter-dot transport. *Semiconductor Science and Technology*, **2006**, 21, 527-531	1.8	13
63	Dense arrays of Ge nanoclusters induced by low-energy ion-beam assisted deposition on Si02 films **2006**,		2
62	Narrowing of ground energy level distribution in an array of InAs/AlAs QDs by post grown annealing. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2006**, 3, 3932-3934		2

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